

Schottky barrier diode

RB751S-40 / RB751V-40

●Applications

High speed switching
For Detection

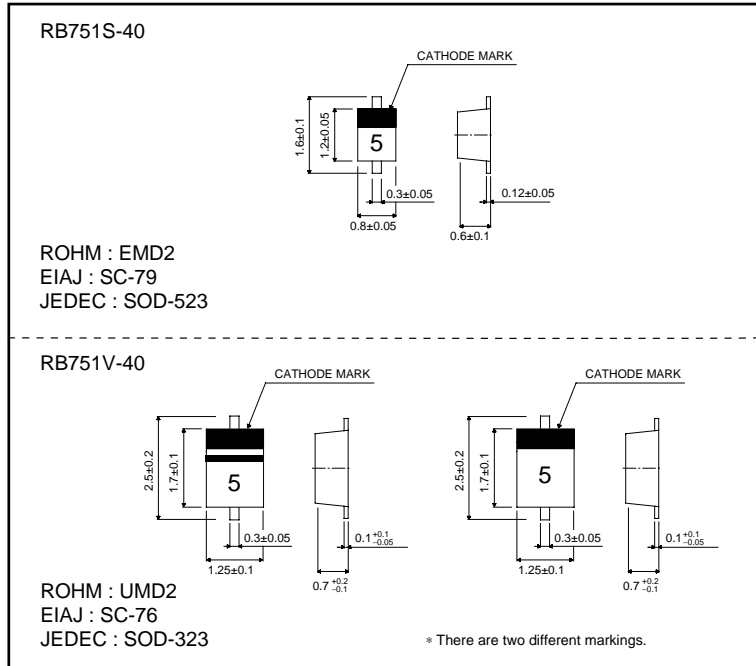
●Features

- 1) Small surface mounting type.
(EMD2, UMD2)
- 2) Low reverse current and low forward voltage.
- 3) High reliability.

●Construction

Silicon epitaxial planar

●External dimensions (Units : mm)



●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	40	V
DC reverse voltage	V_R	30	V
Mean rectifying current	I_o	30	mA
Peak forward surge current*	I_{FSM}	200	mA
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-40~+125	°C

* 60 Hz for 1 μ s

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	-	-	0.37	V	$I_F = 1\text{mA}$
Reverse current	I_R	-	-	0.5	μA	$V_R = 30\text{V}$
Capacitance between terminals	C_T	-	2.0	-	pF	$V_R = 1\text{V}, f = 1\text{MHz}$

Note) ESD sensitive product handling required.

Diodes

●Electrical characteristic curves (Ta = 25°C)

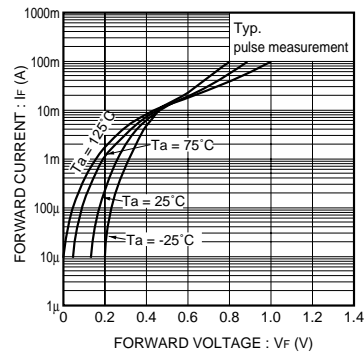


Fig. 1 Forward characteristics

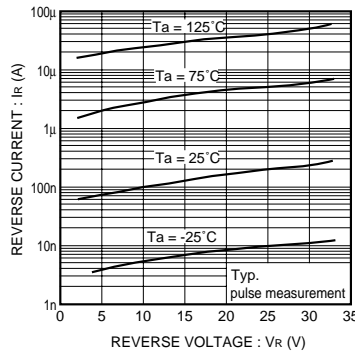


Fig. 2 Reverse characteristics

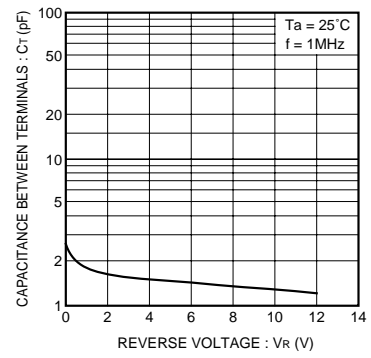


Fig. 3 Capacitance between terminals characteristics